

國立宜蘭大學

101 學年度研究所碩士班考試入學

電子學試題

(電子工程學系碩士班)

准考證號碼：

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《作答注意事項》

1. 請先檢查准考證號碼、座位號碼及答案卷號碼是否相符。
2. 考試時間：100 分鐘。
3. 本試卷共有 6 題，共計 100 分。
4. 請將答案寫在答案卷上。
5. 考試中禁止使用大哥大或其他通信設備。
6. 考試後，請將試題卷及答案卷一併繳交。
7. 本試卷採雙面影印，請勿漏答。
8. 本考科可使用非程式型（不具備儲存程式功能）之電子計算機。

1. Choose the correct answer for the following questions. (40%)

- (1) Diffusion capacitance is existed while  $pn$  junction is under:  
 (A) open circuit (B) reverse bias (C) forward bias (D) barrier.
- (2) Compared with the  $pn$  junction under open circuit, which is correct about  $pn$  junction under forward bias?

- (A) Diffusion current is decreased.  
 (B) Charge stored in depletion region is increased.  
 (C) Width of depletion region is increased.  
 (D) Barrier of depletion region is decreased.

- (3) The addition of  $R_e$  in Fig.1 is used to enhance the:  
 (A) linear region (B) the output resistance  
 (C) the voltage gain (D) the transconductance.
- (4) If the current gain parameter of BJT in active region is represented as  $\beta$ , which is correct about the current gain parameter?

- (A)  $\beta$  is defined as  $I_B/I_C$   
 (B) under the same circuit, the BJT with smaller  $\beta$  will saturate more easily.  
 (C) the value of  $\beta$  is not related to temperature.  
 (D) the current gain in saturation region is less than  $\beta$ .

- (5) For the Fig.2 shown is the current  $i_D$  versus  $v_{DS}$  of NMOS and the load line, which is the best bias point?  
 (A) point A (B) point B (C) point C (D) point D

- (6) Compared with Common-Emitter (CE) amplifier, which is correct about Common-Collector (CC) amplifier?

- (A) larger voltage gain  
 (B) less output resistance  
 (C) bad frequency response  
 (D) often used in differential amplifier

- (7) The circuit shown in Fig.3 is Widlar current source, and it is used to generate

- (A) a small output current using relatively small resistors  
 (B) a large output current using relatively large resistors  
 (C) a small output current using relatively large resistors  
 (D) a large output current using relatively small resistors

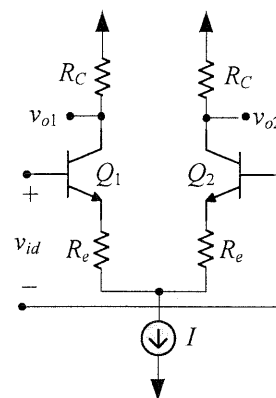


Fig.1

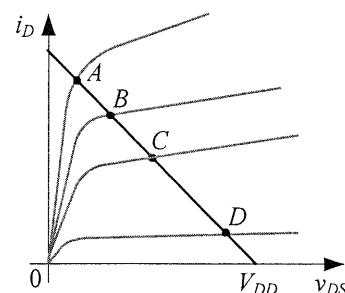


Fig.2

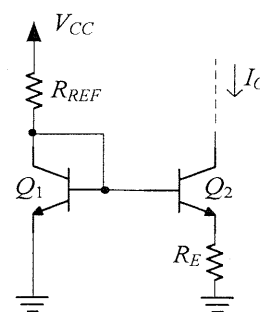


Fig.3

- (8) Compared with CE, the CC-CE configuration shown in Fig.4 has main advantages on
- (A) input resistance decreased and voltage gain increased
  - (B) voltage gain increased and output resistance decreased
  - (C) input resistance increased and bandwidth increased
  - (D) output resistance increased and bandwidth increased

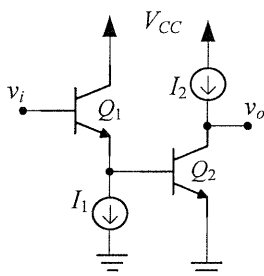


Fig.4

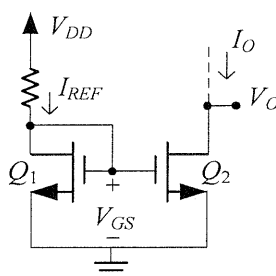


Fig.5

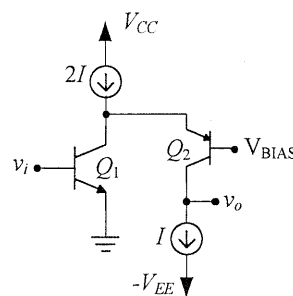


Fig.6

- (9) For the current mirror shown in Fig.5 and  $I_{REF} = 40 \mu\text{A}$ , assume  $Q_1$  and  $Q_2$  are identical with  $V_t = 0.5 \text{ V}$ ,  $\mu_n C_{ox}(W/L) = 20 \mu\text{A}/\text{V}^2$ . If this circuit can work properly, which is the minimum value of voltage  $V_O$  in V? (A) 2.5 (B) 2.0 (C) 1.5 (D) 0.5
- (10) For the folded cascode amplifier shown in Fig.6, assume the current gain parameters and the transconductances of  $Q_1$ ,  $Q_2$  are  $\beta_1$ ,  $\beta_2$  and  $g_{m1}$ ,  $g_{m2}$ , respectively. Then the voltage gain  $A_v = v_o/v_i = ?$
- (A)  $-g_{m2}\beta_1 r_{o1}$  (B)  $-g_{m2}\beta_2 r_{o2}$  (C)  $-g_{m1}\beta_1 r_{o1}$  (D)  $-g_{m1}\beta_2 r_{o2}$

2. The BJT circuit shown in Fig.7 has the following condition:  $V_{CC} = +15 \text{ V}$ ,  $\beta = 100$ ,  $R_{B1} = 100 \text{ k}\Omega$ ,  $R_{B2} = 50 \text{ k}\Omega$ ,  $R_C = 5 \text{ k}\Omega$ ,  $R_E = 2 \text{ k}\Omega$ . Find:
- (a) current  $I_C$ , and
  - (b) its transconductance  $g_m$ .
- (10%)

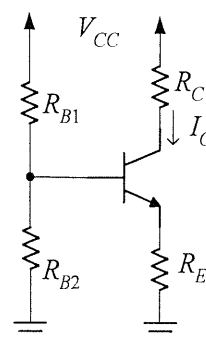


Fig.7

3. For the circuit shown in Fig.8, find:
- (a) transfer function  $V_o(s)/V_i(s)$ .
  - (b) Design the circuit to obtain a dc gain = 20 dB, 3-dB frequency  $\omega_0 = 10\text{k rad/s}$ , and  $R_i = 1 \text{ k}\Omega$ .
- (10%)

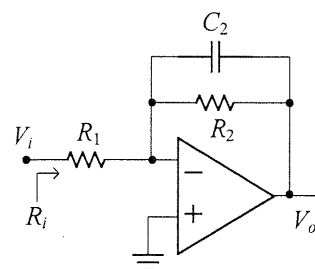


Fig.8

4. For the circuit shown in Fig.9, assume the diodes to be ideal. Analyze and plot the voltage transfer characteristic of the circuit.  
 (10%)

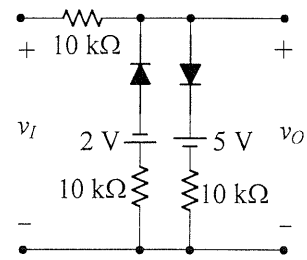
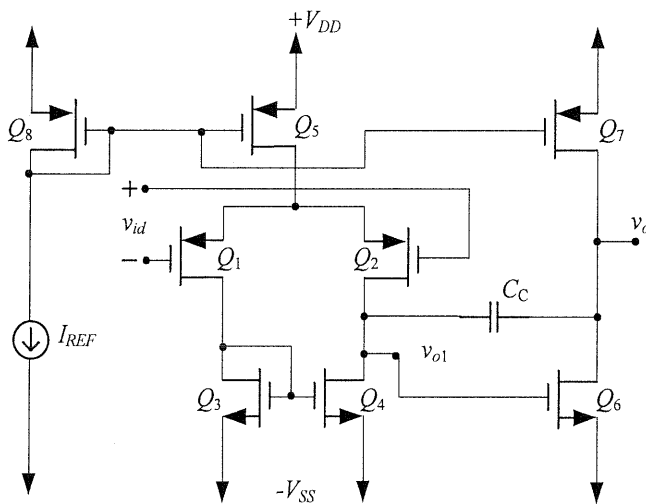


Fig.9

5. The circuit shown in Fig.10 has the following parameters:  $I_{REF} = 200 \mu\text{A}$ ,  $|V_t| = 1 \text{ V}$ ,  $V_{DD} = V_{SS} = 5 \text{ V}$ ,  $\mu_n C_{ox} = 160 \mu\text{A/V}^2$ ,  $\mu_p C_{ox} = 40 \mu\text{A/V}^2$ ,  $|V_A| = 20 \text{ V}$ . Find:  
 (a) the  $|V_{GS}|$  of  $Q_1, Q_3, Q_5$   
 (b) the input common-mode range  
 (c) the transconductance  $g_m$  of  $Q_2$   
 (d) voltage gain  $v_{o1}/v_{id}$ .  
 (20%)



Transistor	$Q_1$	$Q_2$	$Q_3$	$Q_4$	$Q_5$	$Q_6$	$Q_7$	$Q_8$
$W/L$	20/1	20/1	5/1	5/1	40/1	10/1	40/1	40/1

Fig.10

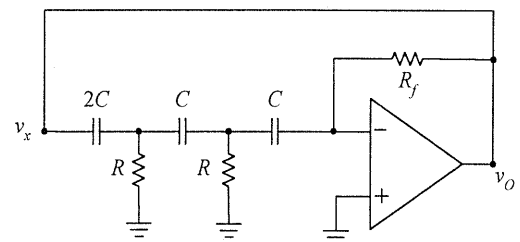


Fig.11

6. For the oscillator circuit shown in Fig.11, (a) find the loop gain  $A\beta = V_o(j\omega)/V_x(j\omega)$ .  
 (b) Find the frequency of oscillation  $\omega_o$  and the minimum required value of  $R_f$  for oscillation to start.  
 (10%)